

Serial No. 09/493,819
Docket No. T36-119817M/RS
(NGB.161)

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AMENDMENTS TO THE CLAIMS:

1-4. (Canceled).

5. (Currently amended) A group III nitride compound semiconductor device according to claim 25 [[3]], wherein said composition ratios of at least Al and In of said intervening layer change continuously in a direction toward said light-emitting layer from said first interface with said buffer layer, so that, a band gap at said second interface of said intervening layer is wider than a band gap of said light-emitting layer.

6-7. (Canceled).

8. (Currently amended) A group II nitride compound semiconductor device according to claim 25 [[3]], wherein said buffer layer comprises $\text{Al}_x\text{Ga}_{1-x}\text{N}$ ($0 \leq X \leq 1$).

9. (Canceled).

10. (Currently amended) A group II nitride compound semiconductor device according to claim 25 [[3]], wherein said composition ratios of said at least Al and In of said intervening layer change from 0.34 for Al and 0.33 for In at said first interface with said buffer layer to 0.11 for Al and 0.28 for In at said second interface with said light-emitting layer.

11. (Currently amended) A group III nitride compound semiconductor device according to claim 25 [[3]], wherein said composition ratios of at least Al and In of said intervening layer change discontinuously in a direction toward said light-emitting layer from said first interface with said buffer layer, so that, a band gap at said second interface of said intervening layer is wider than a band gap of said light-emitting layer.

12-24. (Canceled).

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25. (Previously presented) A group III nitride semiconductor device of a successively laminated structure, comprising:

a substrate;

a buffer layer formed directly on said substrate and having a buffer layer lattice constant;

an intervening layer formed directly on said buffer layer, said intervening layer comprising $\text{Al}_a\text{Ga}_b\text{In}_{1-a-b}\text{N}$, where $0 < a < 1$, $0 < b < 1$, and $a+b < 1$;

a light-emitting layer formed directly on said intervening layer, said light-emitting layer comprising $\text{In}_y\text{Ga}_{1-y}\text{N}$, where $0 < Y < 1$, and having a light-emitting layer lattice constant; and

a p-type clad layer formed directly on said light-emitting layer,

wherein said p-type clad layer comprises an ungraded GaN layer, and

wherein composition ratios of at least Al and In of said intervening layer change from a first interface with said buffer layer to a second interface with said light-emitting layer, such that, a first lattice constant of said intervening layer at said first interface is lattice-matched to said buffer layer and changes to a second lattice constant at said second interface, which is substantially equal to said light-emitting layer lattice constant.